# N-Channel 80 V (D-S) Super Junction Power MOSFET

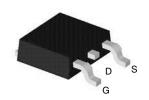
PRODUCT SUMMARY						
V <sub>(BR)DSS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>c</sup>	Q <sub>g</sub> (Typ.)			
80	0.0029 at V <sub>GS</sub> = 10 V	140	90 nC			
	$0.0042$ at $V_{GS} = 4.5 \text{ V}$	90	30 110			

#### **FEATURES**

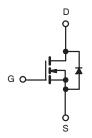
- DT-Trench Power MOSFET
- 100 %  $\rm R_{\rm g}$  and UIS Tested



## TO-252 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
Parameter		Symbol	Limit	Unit			
Gate-Source Voltage		V <sub>GS</sub>	± 20	V			
0 1	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	140				
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 100 °C		90 <sup>a</sup>				
Pulsed Drain Current		I <sub>DM</sub>	560	Α			
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	135					
Avalanche Current		I <sub>AS</sub>			140		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	300	mJ			
Maximum Power Dissination	T <sub>C</sub> = 25 °C	P <sub>D</sub>	425	w			
Maximum Power Dissipation	T <sub>C</sub> = 125 °C	' D	150	VV			
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	10	15	°C/W	
Waximum Junction-to-Ambient	Steady State		20	35		
Maximum Junction-to-Case		$R_{thJC}$	0.75	1.0		

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10 \text{ s.}$



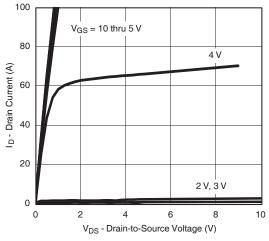


Parameter Symbo		Test Conditions Min.		Typ. <sup>a</sup>	Max.	Unit	
Static				<u>'</u>	<u></u>		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	V		± 100	nA	
		V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			10	μΑ	
		V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			150	1	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V	140			Α	
		$V_{GS} = 10 \text{ V}, I_D = 30 \text{A}$		0.0029	0.0035		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.0034 0.0040		Ω	
Drain-Source On-State Resistance <sup>b</sup>	20(0)	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.0042	0.0055		
Forward Transconductance <sup>b</sup>			85		S		
Dynamic	•			<u>'</u>			
Input Capacitance	C <sub>iss</sub>			10050			
Output Capacitance	C <sub>oss</sub>			3340		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			460			
Total Gate Charge <sup>c</sup>	Qg			98	120		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 64 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{A}$		20		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			30			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 64 V, $R_L$ = 0.6 $\Omega$		18	25		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		55	80	ns	
Fall Time <sup>c</sup>	•			15	22		
Source-Drain Diode Ratings and Cha	racteristics (	T <sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				560	Α	
Diode Forward Voltage V <sub>SD</sub>		I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		0.8	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs		125	196	ns	

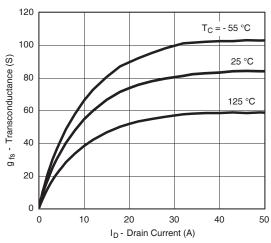
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

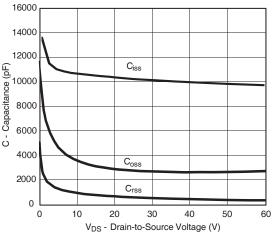
### TYPICAL CHARACTERISTICS (25 °C unless noted)



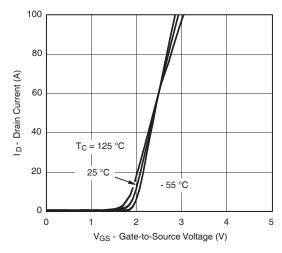
#### **Output Characteristics**



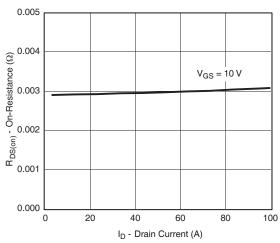
Transconductance



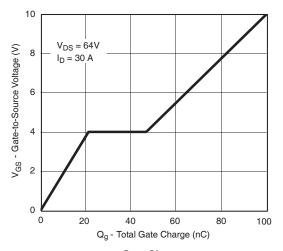
Capacitance



**Transfer Characteristics** 



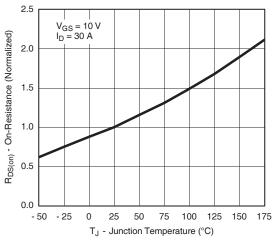
On-Resistance vs. Drain Current



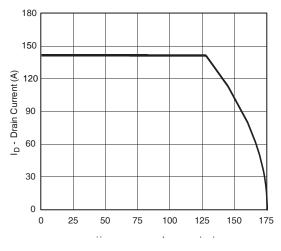
**Gate Charge** 



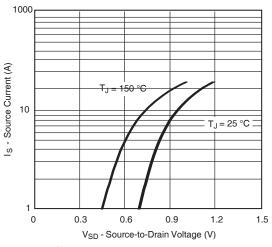
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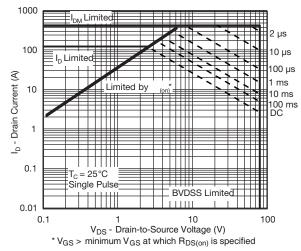
On-Resistance vs. Junction Temperature



Maximum Drain Current vs. Ambient Temperature



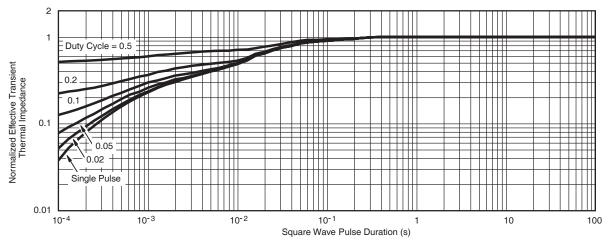
Source-Drain Diode Forward Voltage



Safe Operating Area

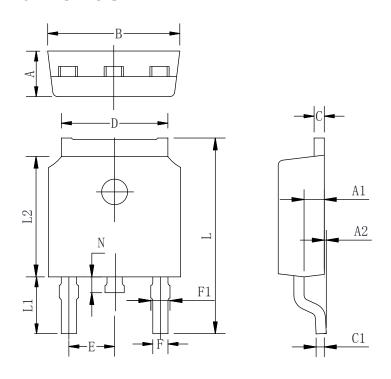


#### THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case

# **TO-252-2L PACKAGE OUTLINE**



## COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
C	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	



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